



Organization:

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Conference Chair:

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Program Chair:

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Program Vice-Chair:

Kai Tak Lam (TSMC)

Shingo Sato (Kansai Univ.)

Workshop:

Mincheol Shin (KAIST)

Yoon-Suk Kim (Samsung)

Hiroki Tokuhira (Kioxia)

Ken Uchida (The Univ. of Tokyo)

Local Arrangements:

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Tomoya Nishimura (Renesas)

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Publication:

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General Affairs:

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Yoshinari Kamakura (Osaka Inst. Tech.)

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Yuki Ohuchi (Fuji Electric)

Kenichiro Sonoda (Renesas)

First Call for Papers

*2026 International Conference on Simulation of
Semiconductor Processes and Devices*

SISPAD2026

September 28 – 30, 2026

(Workshop: September 27)

Kumamoto-jo Hall, Kumamoto, JAPAN

Sponsored by The Japan Society of Applied Physics

Technical Co-sponsored by The IEEE Electron Devices Society



Scope:

This conference provides an opportunity for the presentation and discussion of the latest advances in modeling and simulation of semiconductor devices and processes.

Topics:

- Modeling and simulation of established semiconductor devices, including FinFETs, GAA FETs, ultra-thin SOI devices, TFTs, optoelectronic devices, memories, sensors, power electronic devices, and organic electronic devices
- Modeling and simulation of emerging devices including tunnel FETs, SETs, spintronic devices, straintronic devices, bio-electronic devices, cryogenic CMOS, emerging memories, neuromorphic devices, quantum computing devices, and new material-based devices for various applications
- Modeling and simulation of all sorts of semiconductor processes, including first-principles material design and growth simulation of nano-scale fabrication
- Fundamental aspects of device modeling and simulation, including quantum transport, thermal transport, fluctuation, noise, and reliability
- Compact modeling for circuit simulation, including low-power, high-frequency, and power electronics applications
- Process/device/circuit co-simulation in the context of system design and verification, including for emerging devices
- Modeling and simulation of interconnects, including noise, parasitic effects, and applications for advanced packaging schemes
- Modeling and simulation of equipment, topography, and lithography
- Numerical methods and algorithms, including grid generation, user interface, and visualization
- Enhancement of simulation methodologies, including multi-physics simulation, multi-scale approaches, and the use of artificial intelligence and quantum computing

Abstract Submission:

Authors are invited to submit a two-page abstract (A4 size) including figures. Full submission information will be updated in the Second Call for Papers and the following website:

<https://sispad2026.jp/> (QR code on the right)



Deadline for submission of abstracts: April 10, 2026

Authors of accepted papers will be required to submit a camera-ready four-page manuscript for inclusion in the Conference Proceedings.

For inquiries, please contact:

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